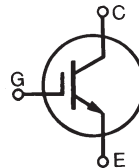


High Voltage IGBT

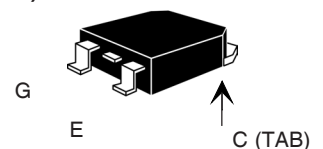
IXGH 16N170
IXGT 16N170

$V_{CES} = 1700 \text{ V}$
 $I_{C25} = 32 \text{ A}$
 $V_{CE(sat)} = 3.5 \text{ V}$
 $t_{fi(typ)} = 290 \text{ ns}$

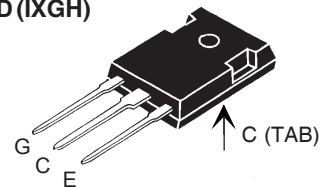


Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	1700	V
V_{CGR}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}; R_{GE} = 1 \text{ M}\Omega$	1700	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$	32	A
I_{C90}	$T_C = 90^\circ\text{C}$	16	A
I_{CM}	$T_C = 25^\circ\text{C}, 1 \text{ ms}$	80	A
SSOA (RBSOA)	$V_{GE} = 15 \text{ V}, T_{VJ} = 125^\circ\text{C}, R_G = 10 \Omega$ Clamped inductive load	$I_{CM} = 40$ @ $0.8 V_{CES}$	A
P_C	$T_C = 25^\circ\text{C}$	190	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
Maximum Lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	$^\circ\text{C}$
Maximum Tab temperature for soldering SMD devices for 10 s		260	$^\circ\text{C}$
M_d	Mounting torque (M3)	1.13/10Nm/lb.in.	
Weight	TO-247 AD	6	g
	TO-268	4	g

TO-268 (IXGT)



TO-247 AD (IXGH)



G = Gate,
E = Emitter,
C = Collector,
TAB = Collector

Features

- International standard packages JEDEC TO-268 and JEDEC TO-247 AD
- High current handling capability
- MOS Gate turn-on - drive simplicity
- Rugged NPT structure
- Molding epoxies meet UL 94 V-0 flammability classification

Applications

- Capacitor discharge & pulser circuits
- AC motor speed control
- DC servo and robot drives
- DC choppers
- Uninterruptible power supplies (UPS)
- Switched-mode and resonant-mode power supplies

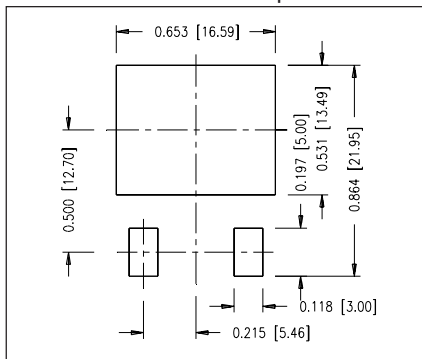
Advantages

- High power density
- Suitable for surface mounting
- Easy to mount with 1 screw, (isolated mounting screw hole)

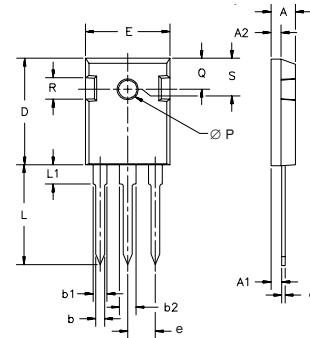
Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
BV_{CES}	$I_C = 250 \mu\text{A}, V_{GE} = 0 \text{ V}$	1700		V
$V_{GE(th)}$	$I_C = 250 \mu\text{A}, V_{CE} = V_{GE}$	3.0		5.0 V
I_{CES}	$V_{CE} = 0.8 \cdot V_{CES}$ $V_{GE} = 0 \text{ V}$			50 μA 500 μA
I_{GES}	$V_{CE} = 0 \text{ V}, V_{GE} = \pm 20 \text{ V}$			$\pm 100 \text{ nA}$
$V_{CE(sat)}$	$I_C = I_{C90}, V_{GE} = 15 \text{ V}$	$T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$	2.7 3.3	3.5 V V

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
g_{fs}	$I_C = I_{C90}; V_{CE} = 10\text{ V}$, Pulse test, $t \leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$	10	14	S
$I_{C(ON)}$	$V_{GE} = 10\text{ V}$, $V_{CE} = 10\text{ V}$		60	A
C_{ies}	$V_{CE} = 25\text{ V}$, $V_{GE} = 0\text{ V}$, $f = 1\text{ MHz}$		1700	pF
C_{oes}			83	pF
C_{res}			30	pF
Q_g	$I_C = I_{C90}$, $V_{GE} = 15\text{ V}$, $V_{CE} = 0.5 V_{CES}$		78	nC
Q_{ge}			13	nC
Q_{gc}			24	nC
$t_{d(on)}$	Inductive load, $T_J = 25^\circ\text{C}$ $I_C = I_{C90}$, $V_{GE} = 15\text{ V}$ $V_{CE} = 0.8 V_{CES}$, $R_G = R_{off} = 10\text{ }\Omega$ Remarks: Switching times may increase for V_{CE} (Clamp) $> 0.8 \cdot V_{CES}$, higher T_J or increased R_G	45		ns
t_{ri}		48		ns
$t_{d(off)}$		200	400	ns
t_{fi}		290	500	ns
E_{off}		8	12	mJ
$t_{d(on)}$	Inductive load, $T_J = 125^\circ\text{C}$ $I_C = I_{C90}$, $V_{GE} = 15\text{ V}$ $V_{CE} = 0.8 V_{CES}$, $R_G = R_{off} = 10\text{ }\Omega$ Remarks: Switching times may increase for V_{CE} (Clamp) $> 0.8 \cdot V_{CES}$, higher T_J or increased R_G	48		ns
t_{ri}		42		ns
E_{on}		1.5		mJ
$t_{d(off)}$		200		ns
t_{fi}		360		ns
E_{off}		10		mJ
R_{thJC}				0.65 K/W
R_{thCK}	(TO-247)		0.25	K/W

Min Recommended Footprint

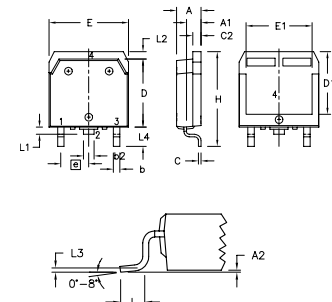


TO-247 AD Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A ₁	2.2	2.54	.087	.102
A ₂	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b ₁	1.65	2.13	.065	.084
b ₂	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
ØP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	.242	BSC

TO-268 Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.9	5.1	.193	.201
A ₁	2.7	2.9	.106	.114
A ₂	.02	.25	.001	.010
b	1.15	1.45	.045	.057
b ₁	1.9	2.1	.075	.083
C	.4	.65	.016	.026
D	13.80	14.00	.543	.551
E	15.85	16.05	.624	.632
E ₁	13.3	13.6	.524	.535
e	5.45	BSC	.215	BSC
H	18.70	19.10	.736	.752
L	2.40	2.70	.094	.106
L1	1.20	1.40	.047	.055
L2	1.00	1.15	.039	.045
L3		0.25 BSC		.010 BSC
L4	3.80	4.10	.150	.161

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592 4,881,106 5,017,508 5,049,961 5,187,117 5,486,715 6,306,728B1 6,259,123B1 6,306,728B1
 4,850,072 4,931,844 5,034,796 5,063,307 5,237,481 5,381,025 6,404,065B1 6,162,665 6,534,343

Fig. 1. Output Characteristics
@ 25 Deg. C

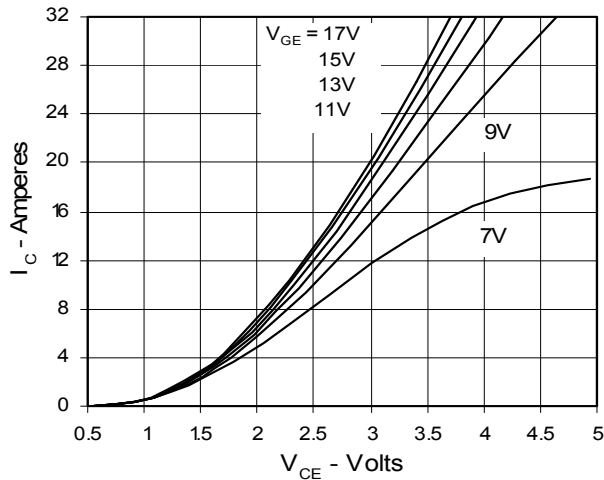


Fig. 2. Extended Output Characteristics
@ 25 Deg. C

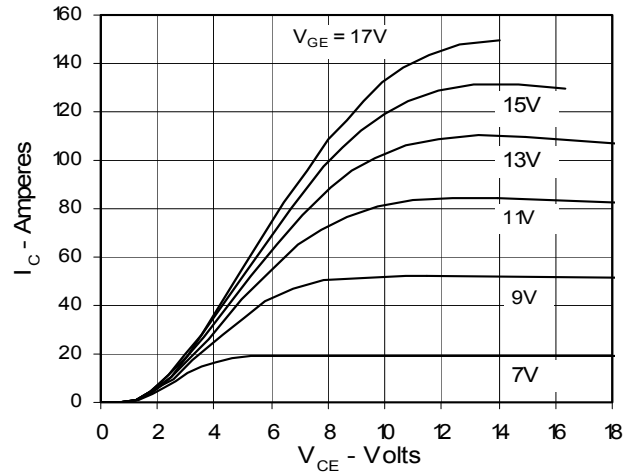


Fig. 3. Output Characteristics
@ 125 Deg. C

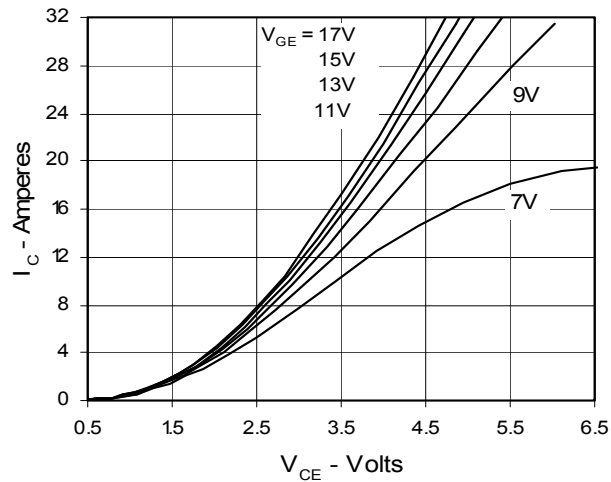


Fig. 4. Temperature Dependence of $V_{CE(sat)}$

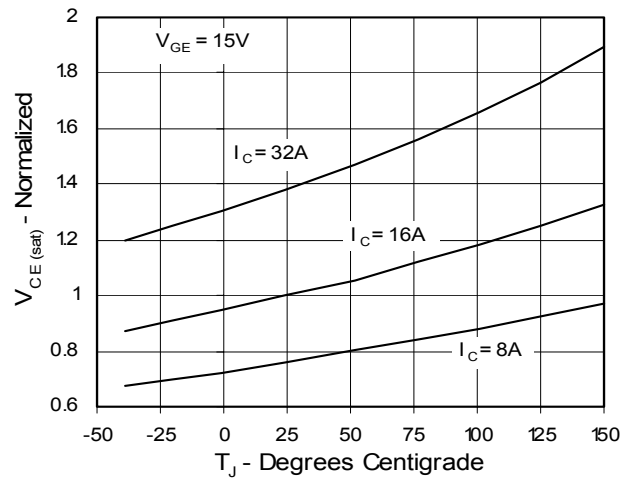


Fig. 5. Collector-to-Emitter Voltage
vs. Gate-to-Emitter voltage

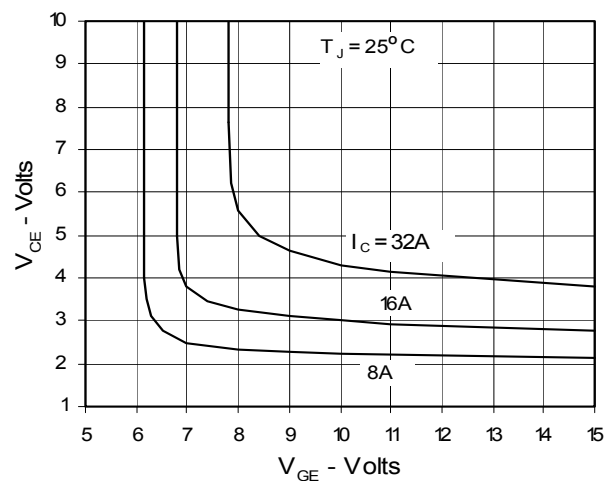


Fig. 6. Input Admittance

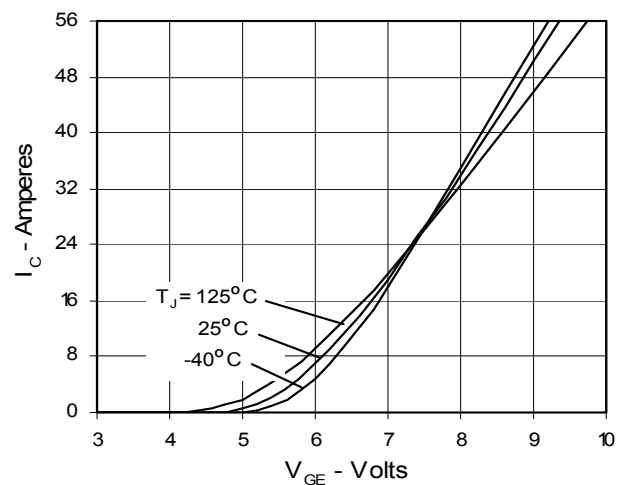


Fig. 7. Transconductance

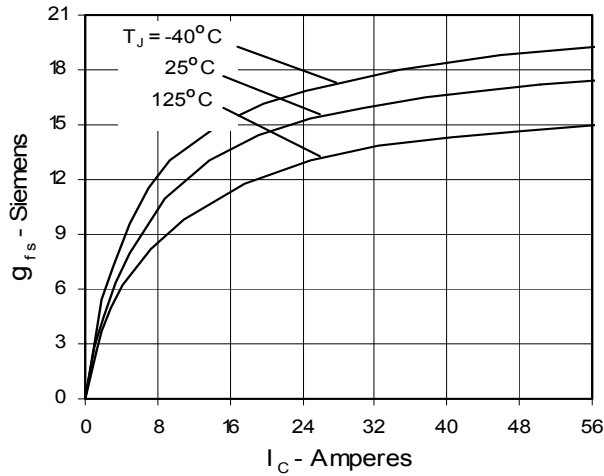


Fig. 8. Dependence of E_{off} on R_G

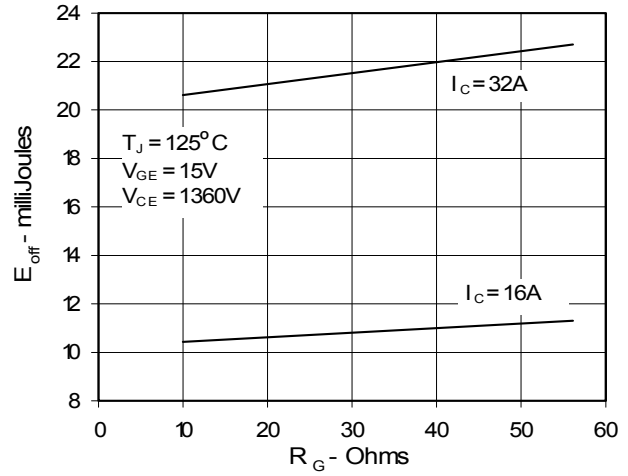


Fig. 9. Dependence of E_{off} on I_C

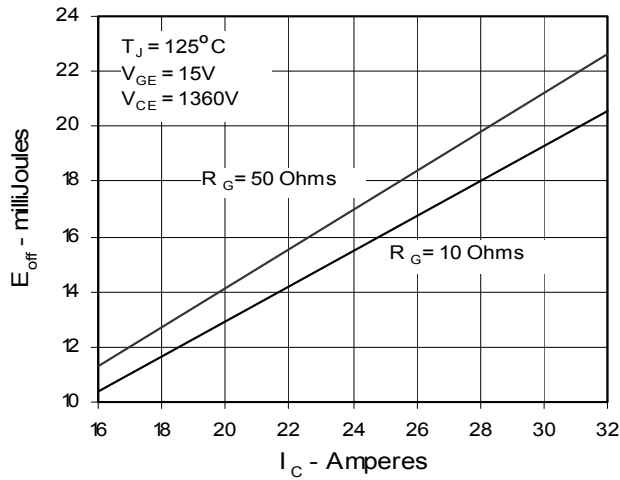


Fig. 10. Dependence of E_{off} on Temperature

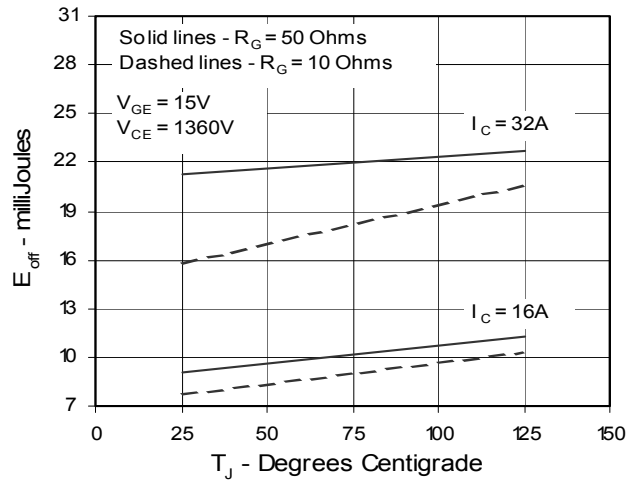


Fig. 11. Gate Charge

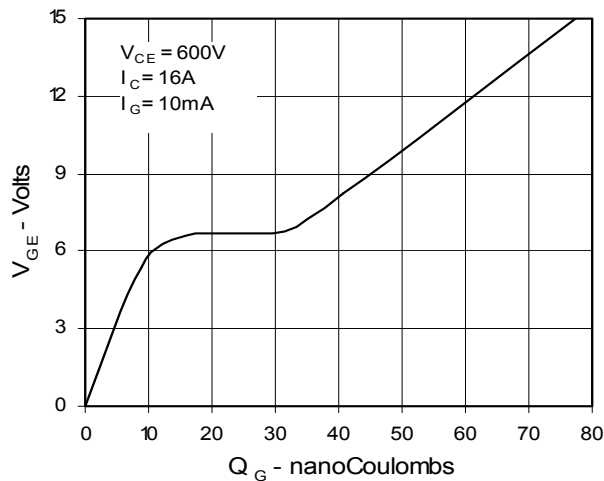
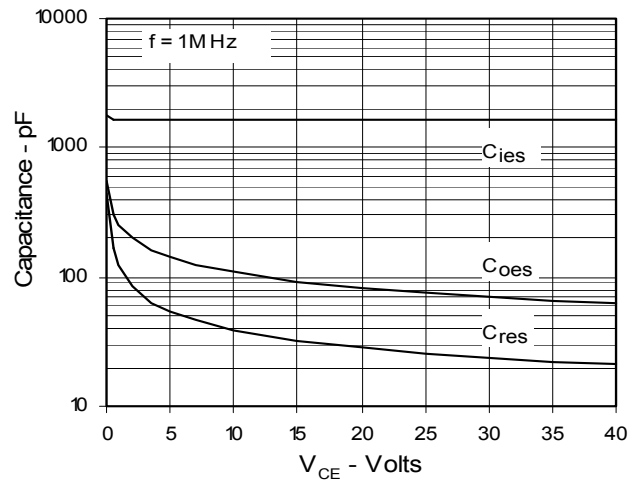


Fig. 12. Capacitance



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4,850,072 4,931,844 5,034,796 5,063,307 5,237,481 5,381,025 6,404,065B1 6,162,665 6,534,343

Fig. 13. Maximum Transient Thermal Resistance

